

K6R4016C1C-C, K6R4016C1C-E, K6R4016C1C-I CMOS SRAM

Document Title

256Kx16 Bit High Speed Static RAM(5V Operating).
Operated at Extended and Industrial Temperature Ranges.

Revision History

RevNo.	History	Draft Data	Remark
Rev. 0.0	Initial release with Preliminary.	Feb. 12. 1999	Preliminary
Rev. 1.0	1.1 Removed Low power Version. 1.2 Removed Data Retention Characteristics 1.3 Changed I _{SB1} to 20mA	Mar. 29. 1999	Preliminary
Rev. 2.0	2.1 Relax D.C parameters.	Aug. 19. 1999	Preliminary

Item		Previous	Current
I _{CC}	12ns	190mA	200mA
	15ns	185mA	195mA
	20ns	180mA	190mA

2.2 Relax Absolute Maximum Rating.

Item	Previous	Current
Voltage on Any Pin Relative to V _{SS}	-0.5 to 7.0	-0.5 to V _{CC} +0.5

Rev.3.0	3.1 Delete Preliminary 3.2 Update D.C parameters and 10ns part.	Mar. 27. 2000	Final
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	Previous			Current		
	I _{CC}	I _{SB}	I _{SB1}	I _{CC}	I _{SB}	I _{SB1}
10ns	-	70mA	20mA	185mA	60mA	10mA
12ns	200mA			175mA		
15ns	195mA			165mA		
20ns	190mA			160mA		

3.3 Added Extended temperature range

The attached data sheets are prepared and approved by SAMSUNG Electronics. SAMSUNG Electronics CO., LTD. reserve the right to change the specifications. SAMSUNG Electronics will evaluate and reply to your requests and questions on the parameters of this device. If you have any questions, please contact the SAMSUNG branch office near your office, call or contact Headquarters.

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256K x 16 Bit High-Speed CMOS Static RAM

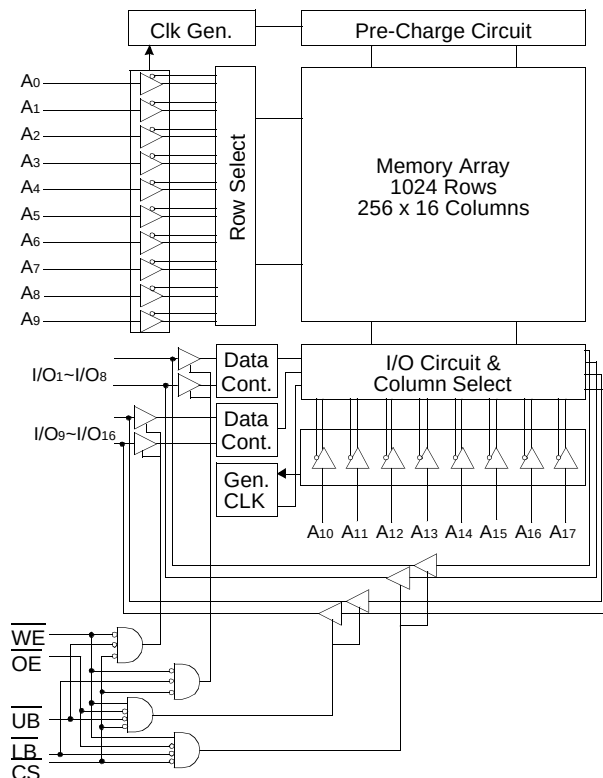
FEATURES

- Fast Access Time 10,12,15,20ns(Max.)
- Low Power Dissipation
 - Standby (TTL) : 60mA(Max.)
 - (CMOS) : 10mA(Max.)
 - Operating K6R4016C1C-10 : 185mA(Max.)
 - K6R4016C1C-12 : 175mA(Max.)
 - K6R4016C1C-15 : 165mA(Max.)
 - K6R4016C1C-20 : 160mA(Max.)
- Single 5.0V $\pm 10\%$ Power Supply
- TTL Compatible Inputs and Outputs
- I/O Compatible with 3.3V Device
- Fully Static Operation
 - No Clock or Refresh required
- Three State Outputs
- Center Power/Ground Pin Configuration
- Data Byte Control : LB : I/O1~ I/O8, UB : I/O9~ I/O16
- Standard Pin Configuration
 - K6R4016C1C-J : 44-SOJ-400
 - K6R4016C1C-T : 44-TSOP2-400BF
 - K6R4016C1C-F : 48-Fine pitch BGA with 0.75 Ball pitch

GENERAL DESCRIPTION

The K6R4016C1C is a 4,194,304-bit high-speed Static Random Access Memory organized as 262,144 words by 16 bits. The K6R4016C1C uses 16 common input and output lines and has an output enable pin which operates faster than address access time at read cycle. Also it allows that lower and upper byte access by data byte control(UB, LB). The device is fabricated using SAMSUNG's advanced CMOS process and designed for high-speed circuit technology. It is particularly well suited for use in high-density high-speed system applications. The K6R4016C1C is packaged in a 400mil 44-pin plastic SOJ or TSOP(II) forward or 48 Fine pitch BGA.

FUNCTIONAL BLOCK DIAGRAM

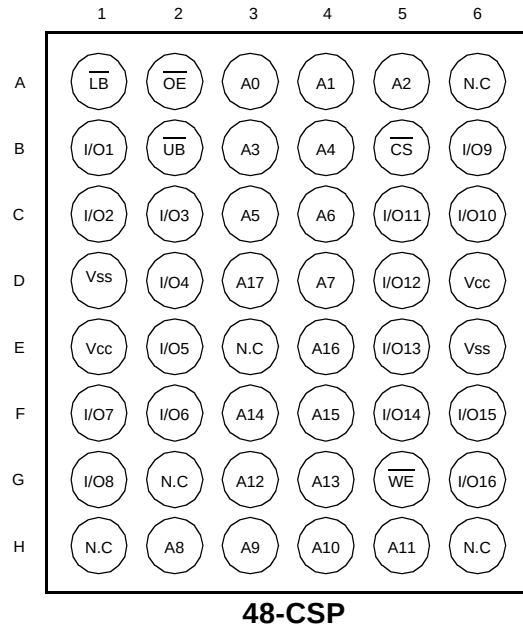
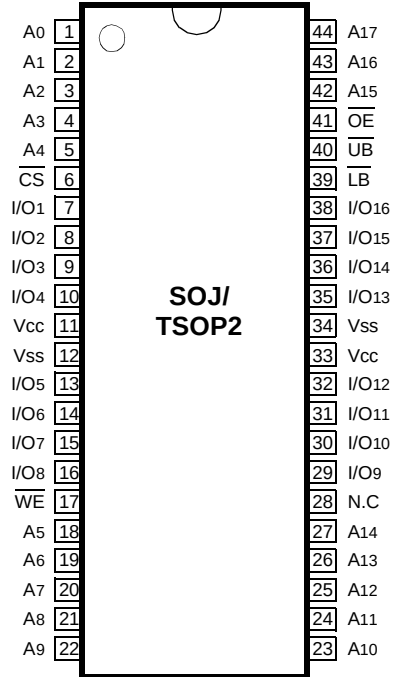


ORDERING INFORMATION

K6R4016C1C-C10/C12/C15/C20	Commercial Temp.
K6R4016C1C-E10/E12/E15/E20	Extended Temp.
K6R4016C1C-I10/I12/I15/I20	Industrial Temp.

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PIN CONFIGURATION (Top View)



PIN FUNCTION

Pin Name	Pin Function
A ₀ - A ₁₇	Address Inputs
$\overline{WE}$	Write Enable
$\overline{CS}$	Chip Select
$\overline{OE}$	Output Enable
$\overline{LB}$	Lower-byte Control(I/O ₁ ~I/O ₈)
$\overline{UB}$	Upper-byte Control(I/O ₉ ~I/O ₁₆)
I/O ₁ ~ I/O ₁₆	Data Inputs/Outputs
Vcc	Power(+5.0V)
Vss	Ground
N.C	No Connection

ABSOLUTE MAXIMUM RATINGS*

Parameter		Symbol	Rating	Unit
Voltage on Any Pin Relative to Vss		V _{IN} , V _{OUT}	-0.5 to Vcc+0.5	V
Voltage on Vcc Supply Relative to Vss		Vcc	-0.5 to 7.0	V
Power Dissipation		P _D	1.0	W
Storage Temperature		T _{STG}	-65 to 150	°C
Operating Temperature	Commercial	T _A	0 to 70	°C
	Extended	T _A	-25 to 85	°C
	Industrial	T _A	-40 to 85	°C

* Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

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RECOMMENDED DC OPERATING CONDITIONS*(TA=0 to 70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply Voltage	V _{CC}	4.5	5.0	5.5	V
Ground	V _{SS}	0	0	0	V
Input High Voltage	V _{IH}	2.2	-	V _{CC} +0.5***	V
Input Low Voltage	V _{IL}	-0.5**	-	0.8	V

* The above parameters are also guaranteed at extended and industrial temperature range.

** V_{IL}(Min) = -2.0V a.c(Pulse Width ≤ 8ns) for I ≤ 20mA.

*** V_{IH}(Max) = V_{CC} + 2.0V a.c (Pulse Width ≤ 8ns) for I ≤ 20mA.

DC AND OPERATING CHARACTERISTICS*(TA=0 to 70°C, V_{CC}= 5.0V±10%, unless otherwise specified)

Parameter	Symbol	Test Conditions			Min	Max	Unit
Input Leakage Current	I _{LI}	V _{IN} =V _{SS} to V _{CC}			-2	2	μA
Output Leakage Current	I _{LO}	CS=V _{IH} or $\overline{\text{OE}}$ =V _{IH} or $\overline{\text{WE}}$ =V _{IL} V _{OUT} = V _{SS} to V _{CC}			-2	2	μA
Operating Current	I _{CC}	Min. Cycle, 100% Duty CS=V _{IL} , V _{IN} =V _{IH} or V _{IL} , I _{OUT} =0mA	Com.	10ns	-	185	mA
				12ns	-	175	
				15ns	-	165	
				20ns	-	160	
			Ext. Ind.	10ns	-	200	
				12ns	-	190	
				15ns	-	180	
				20ns	-	175	
Standby Current	I _{SB}	Min. Cycle, $\overline{\text{CS}}$ =V _{IH}			-	60	mA
	I _{SB1}	f=0MHz, $\overline{\text{CS}}\geq\text{V}_{\text{CC}}-0.2\text{V}$, V _{IN} ≥V _{CC} -0.2V or V _{IN} ≤0.2V			-	10	
Output Low Voltage Level	V _{OL}	I _{OL} =8mA			-	0.4	V
Output High Voltage Level	V _{OH}	I _{OH} =-4mA			2.4	-	V
	V _{OH1} **	I _{OH1} =-0.1mA			-	3.95	V

* The above parameters are also guaranteed at extended and industrial temperature range.

** V_{CC}=5.0V±5%, Temp.=25°C.

CAPACITANCE*(TA=25°C, f=1.0MHz)

Item	Symbol	Test Conditions	MIN	Max	Unit
Input/Output Capacitance	C _{I/O}	V _{I/O} =0V	-	8	pF
Input Capacitance	C _{IN}	V _{IN} =0V	-	7	pF

* Capacitance is sampled and not 100% tested.

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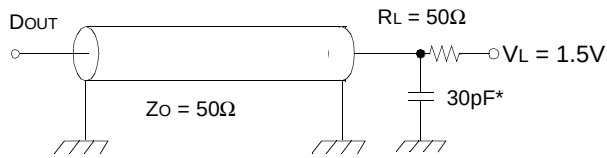
AC CHARACTERISTICS (TA=0 to 70°C, VCC=5.0V±10%, unless otherwise noted.)

TEST CONDITIONS*

Parameter	Value
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	3ns
Input and Output timing Reference Levels	1.5V
Output Loads	See below

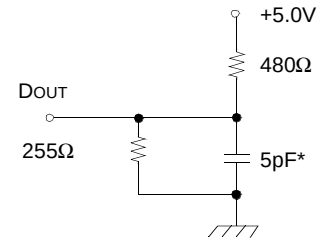
* The above test conditions are also applied at extended and industrial temperature range.

Output Loads(A)



Output Loads(B)

for tHZ, tLZ, tWHZ, tOW, tOLZ & tOHZ



* Capacitive Load consists of all components of the test environment.

* Including Scope and Jig Capacitance

READ CYCLE*

Parameter	Symbol	K6R4016C1C-10		K6R4016C1C-12		K6R4016C1C-15		K6R4016C1C-20		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Read Cycle Time	tRC	10	-	12	-	15	-	20	-	ns
Address Access Time	tAA	-	10	-	12	-	15	-	20	ns
Chip Select to Output	tCO	-	10	-	12	-	15	-	20	ns
Output Enable to Valid Output	tOE	-	5	-	6	-	7	-	9	ns
$\overline{UB}$, $\overline{LB}$ Access Time	tBA	-	5	-	6	-	7	-	9	ns
Chip Enable to Low-Z Output	tLZ	3	-	3	-	3	-	3	-	ns
Output Enable to Low-Z Output	tOLZ	0	-	0	-	0	-	0	-	ns
$\overline{UB}$, $\overline{LB}$ Enable to Low-Z Output	tBLZ	0	-	0	-	0	-	0	-	ns
Chip Disable to High-Z Output	tHZ	0	5	0	6	0	7	0	9	ns
Output Disable to High-Z Output	tOHZ	0	5	0	6	0	7	0	9	ns
$\overline{UB}$, $\overline{LB}$ Disable to High-Z Output	tBHZ	0	5	0	6	0	7	0	9	ns
Output Hold from Address	tOH	3	-	3	-	3	-	3	-	ns

* The above parameters are also guaranteed at extended and industrial temperature range.

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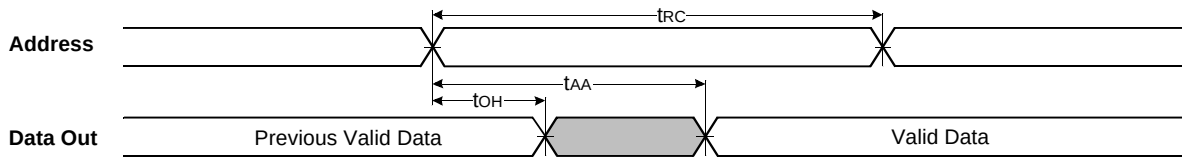
WRITE CYCLE*

Parameter	Symbol	K6R4016C1C-10		K6R4016C1C-12		K6R4016C1C-15		K6R4016C1C-20		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
Write Cycle Time	t _{WC}	10	-	12	-	15	-	20	-	ns
Chip Select to End of Write	t _{CW}	7	-	8	-	10	-	12	-	ns
Address Set-up Time	t _{AS}	0	-	0	-	0	-	0	-	ns
Address Valid to End of	t _{AW}	7	-	8	-	10	-	12	-	ns
Write Pulse Width($\overline{\text{OE}}$ High)	t _{WP}	7	-	8	-	10	-	12	-	ns
Write Pulse Width($\overline{\text{OE}}$ Low)	t _{WP1}	10	-	12	-	15	-	20	-	ns
$\overline{\text{UB}}$, $\overline{\text{LB}}$ Valid to End of	t _{BW}	7	-	8	-	10	-	12	-	ns
Write Recovery Time	t _{WR}	0	-	0	-	0	-	0	-	ns
Write to Output High-Z	t _{WHZ}	0	5	0	6	0	7	0	9	ns
Data to Write Time Overlap	t _{DW}	5	-	6	-	7	-	9	-	ns
Data Hold from Write Time	t _{DH}	0	-	0	-	0	-	0	-	ns
End Write to Output Low-Z	t _{OW}	3	-	3	-	3	-	3	-	ns

* The above parameters are also guaranteed at extended and industrial temperature range.

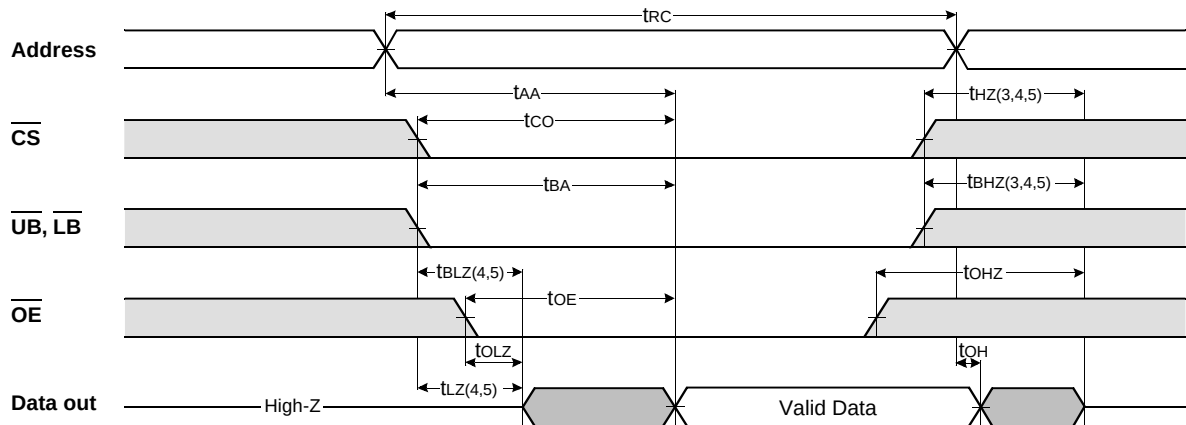
TIMMING DIAGRAMS

TIMING WAVEFORM OF READ CYCLE(1) (Address Controlled, $\overline{\text{CS}}=\overline{\text{OE}}=V_{\text{IL}}$, $\overline{\text{WE}}=V_{\text{IH}}$, $\overline{\text{UB}}$, $\overline{\text{LB}}=V_{\text{IL}}$)



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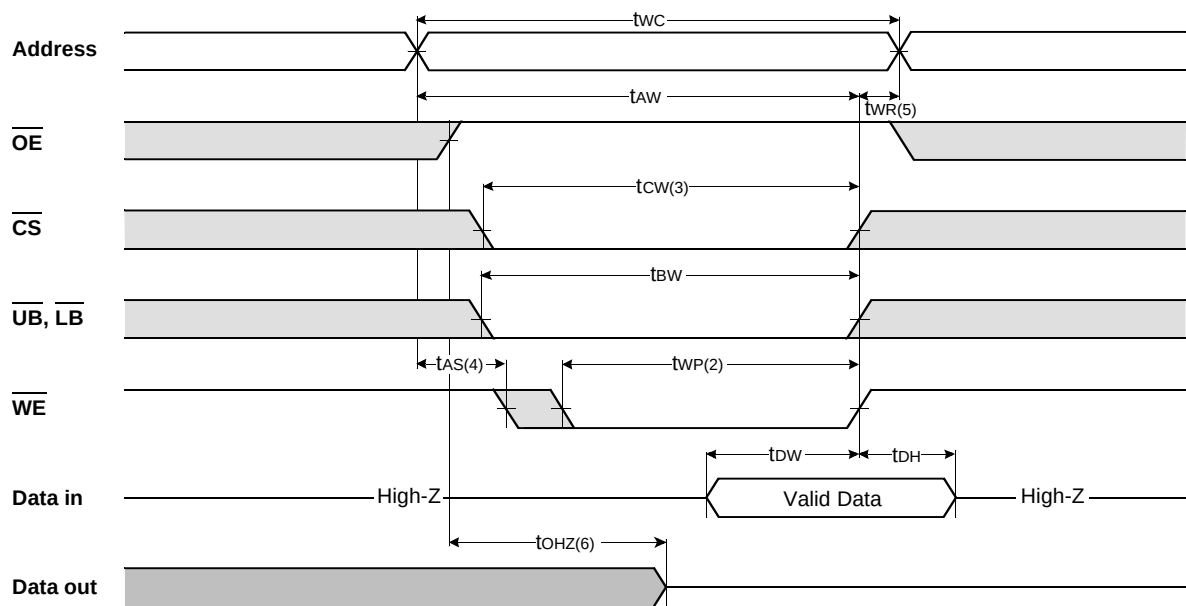
TIMING WAVEFORM OF READ CYCLE(2) ($\overline{WE}=V_{IH}$)



NOTES(READ CYCLE)

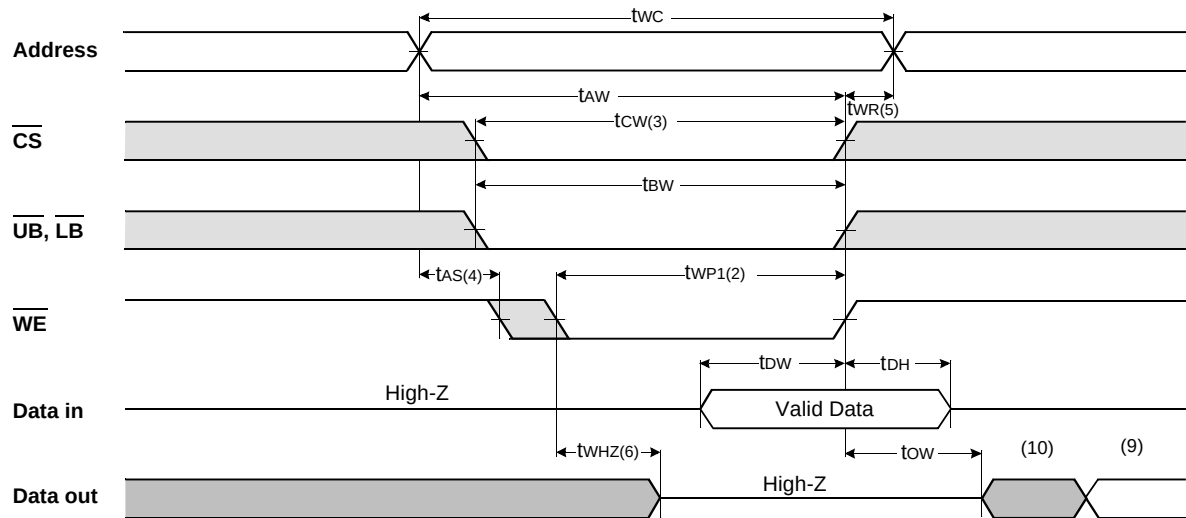
1. $\overline{WE}$ is high for read cycle.
2. All read cycle timing is referenced from the last valid address to the first transition address.
3. t_{HZ} and t_{OHZ} are defined as the time at which the outputs achieve the open circuit condition and are not referenced to V_{OH} or V_{OL} levels.
4. At any given temperature and voltage condition, $t_{HZ}(\text{Max.})$ is less than $t_{LZ}(\text{Min.})$ both for a given device and from device to device.
5. Transition is measured $\pm 200\text{mV}$ from steady state voltage with Load(B). This parameter is sampled and not 100% tested.
6. Device is continuously selected with $\overline{CS}=V_{IL}$.
7. Address valid prior to coincident with $\overline{CS}$ transition low.
8. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.

TIMING WAVEFORM OF WRITE CYCLE(1) ($\overline{OE}$ Clock)

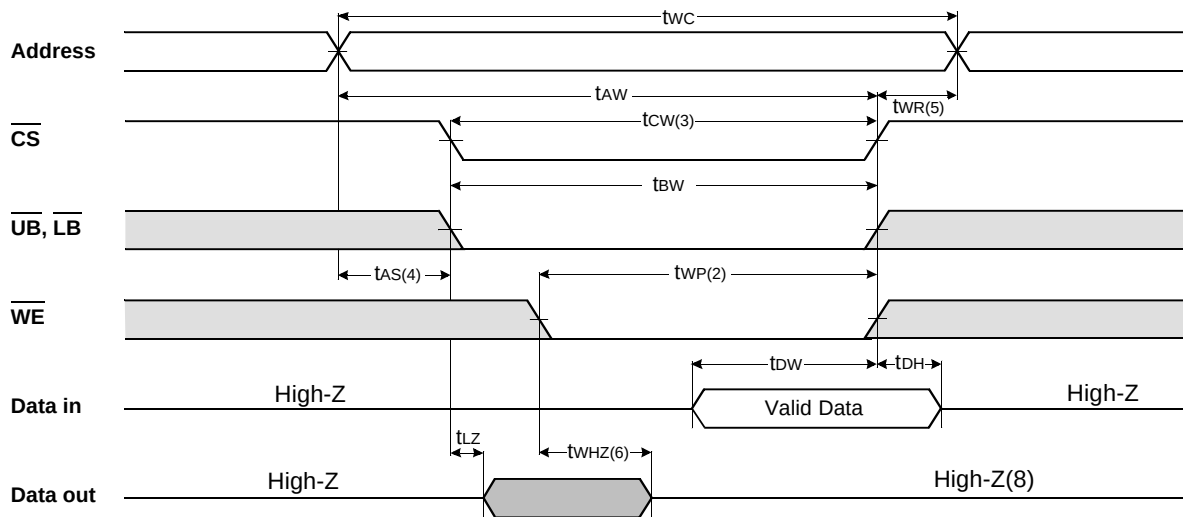


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TIMING WAVEFORM OF WRITE CYCLE(2) ($\overline{OE}$ = Low fixed)

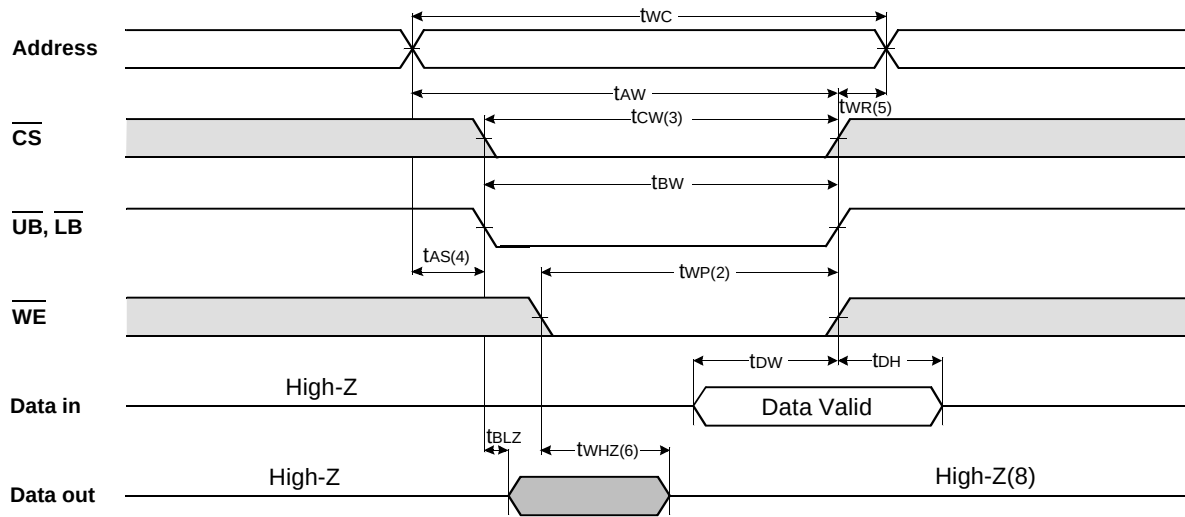


TIMING WAVEFORM OF WRITE CYCLE(3) ($\overline{CS}$ = Controlled)



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TIMING WAVEFORM OF WRITE CYCLE(4) ($\overline{UB}$, $\overline{LB}$ Controlled)



NOTES(WRITE CYCLE)

1. All write cycle timing is referenced from the last valid address to the first transition address.
2. A write occurs during the overlap of a low $\overline{CS}$, $\overline{WE}$, $\overline{LB}$ and $\overline{UB}$. A write begins at the latest transition $\overline{CS}$ going low and $\overline{WE}$ going low ; A write ends at the earliest transition $\overline{CS}$ going high or $\overline{WE}$ going high. t_{WP} is measured from the beginning of write to the end of write.
3. t_{CW} is measured from the later of $\overline{CS}$ going low to end of write.
4. t_{AS} is measured from the address valid to the beginning of write.
5. t_{WR} is measured from the end of write to the address change. t_{WR} applied in case a write ends as $\overline{CS}$ or $\overline{WE}$ going high.
6. If OE, $\overline{CS}$ and $\overline{WE}$ are in the Read Mode during this period, the I/O pins are in the output low-Z state. Inputs of opposite phase of the output must not be applied because bus contention can occur.
7. For common I/O applications, minimization or elimination of bus contention conditions is necessary during read and write cycle.
8. If $\overline{CS}$ goes low simultaneously with $\overline{WE}$ going or after $\overline{WE}$ going low, the outputs remain high impedance state.
9. Dout is the read data of the new address.
10. When $\overline{CS}$ is low : I/O pins are in the output state. The input signals in the opposite phase leading to the output should not be applied.

FUNCTIONAL DESCRIPTION

$\overline{CS}$	$\overline{WE}$	$\overline{OE}$	$\overline{LB}$	$\overline{UB}$	Mode	I/O Pin		Supply Current
						I/O ₁ ~I/O ₈	I/O ₉ ~I/O ₁₆	
H	X	X*	X	X	Not Select	High-Z	High-Z	I _{SB} , I _{SB1}
L	H	H	X	X	Output Disable	High-Z	High-Z	I _{CC}
L	X	X	H	H	Read	DOUT	High-Z	I _{CC}
L	H	L	L	H		High-Z	DOUT	
L	H	L	L	L		DOUT	DOUT	
L	L	X	L	H	Write	DIN	High-Z	I _{CC}
L	L	X	H	L		High-Z	DIN	
L	L	X	L	L		DIN	DIN	

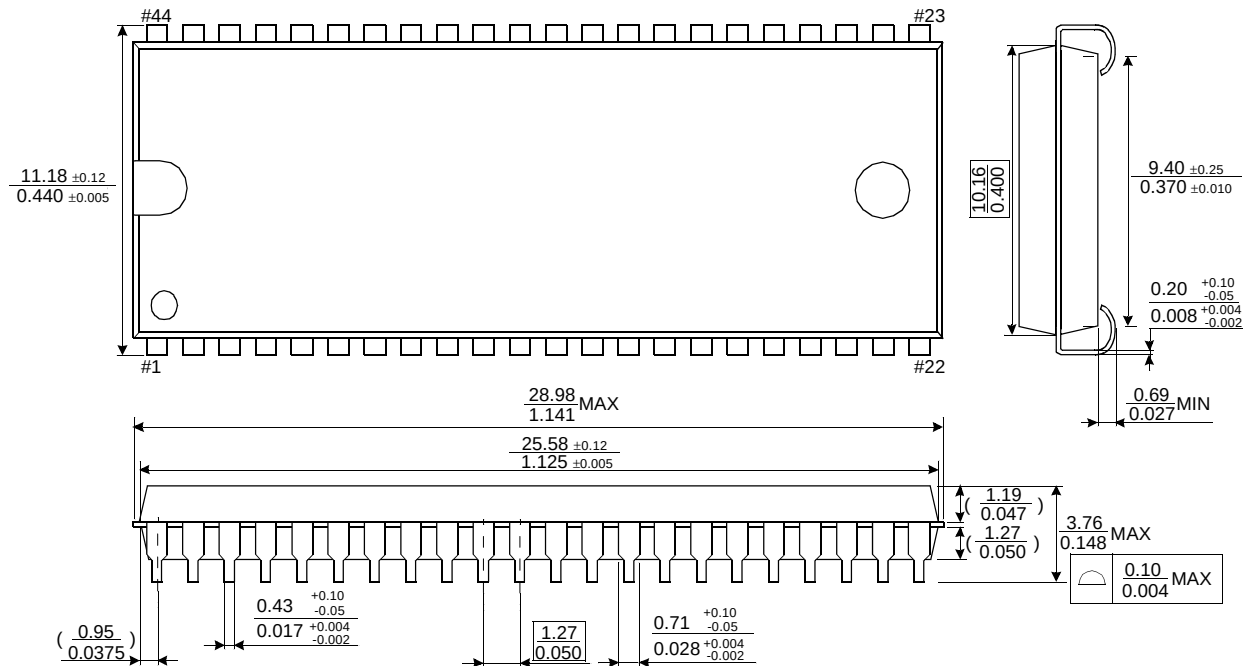
* X means Don't Care.

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PACKAGE DIMENSIONS

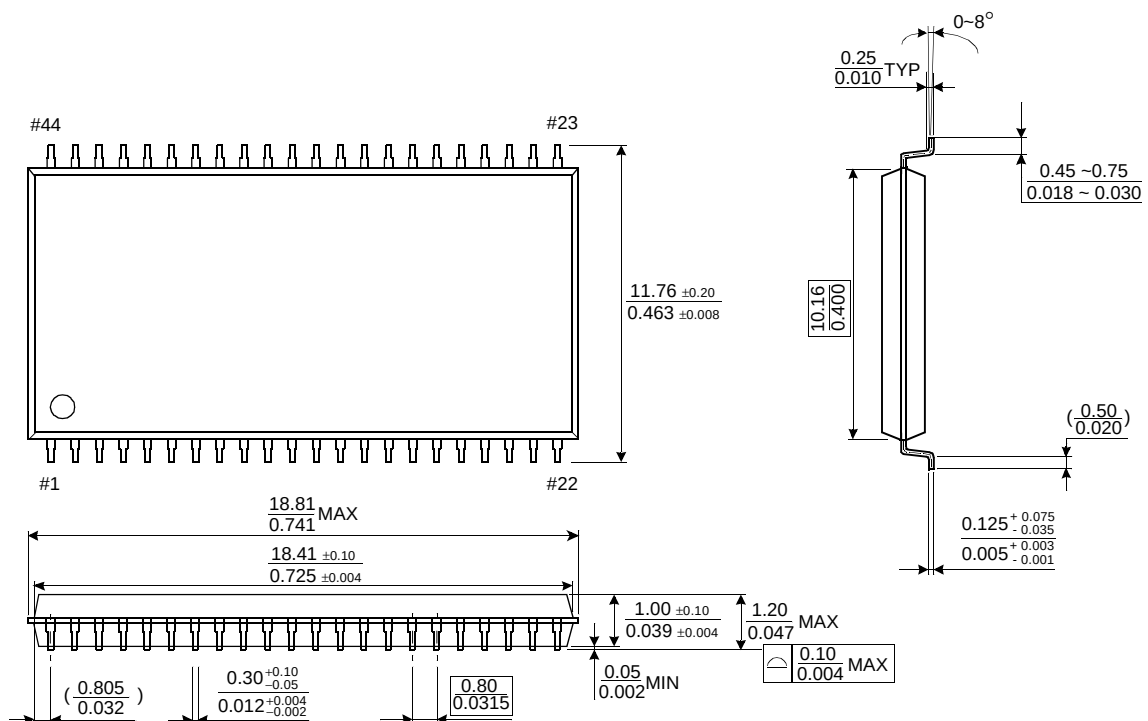
Units: millimeters/Inches

44-SOJ-400



44-TSOP2-400BF

Units: millimeters/Inches



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PACKAGE DIMENSIONS

Units : millimeter.

